Ordering number : ENA1821A

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

MOSFET : P-Channel Silicon MOSFET
SBD : Schottky Barrier Diode

EMH2801 — General-Purpose Switching Device Applications

Features

- Composite type with a P-Channel Sillicon MOSFET and a Schottky Barrier Diode contained in one package facilitating high-density mounting
- [MOSFET] · Low ON-resistance
- [SBD] · Small switching noise
- Halogen free compliance
- 1.8V drive
- Low forward voltage (I_F=2.0A, V_F max=0.46V)

Specifications

Absolute Maximum Ratings at Ta=25°C

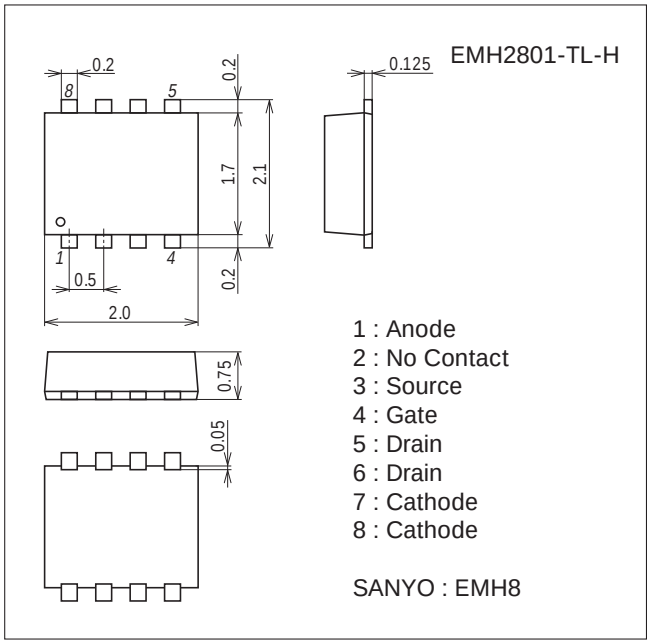
Parameter	Symbol	Conditions	Ratings	Unit
[MOSFET]				
Drain-to-Source Voltage	V_{DSS}		−20	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		−3	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	−20	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm^2×0.8mm) 1unit	1.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +125	°C

Continued on next page.

This product is designed to “ESD immunity < 200V*”, so please take care when handling.
* Machine Model

Package Dimensions

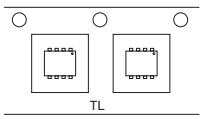
unit : mm (typ)
7045-007



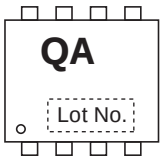
Product & Package Information

- Package : EMH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

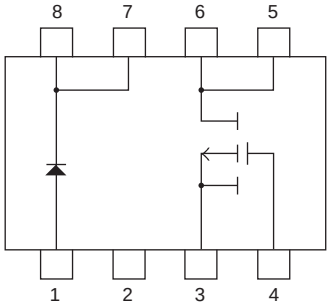
Packing Type : TL



Marking



Electrical Connection



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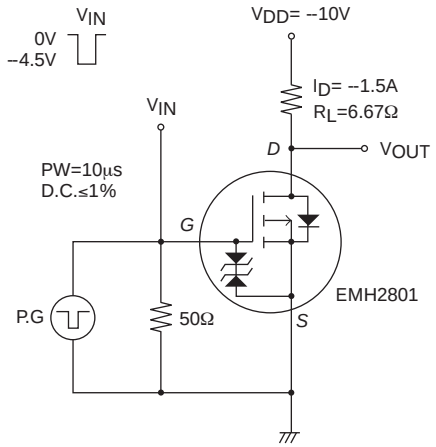
Parameter	Symbol	Conditions	Ratings	Unit
[SBD]				
Repetitive Peak Reverse Voltage	V_{RRM}		15	V
Nonrepetitive Peak Reverse Surge Voltage	V_{RSM}		15	V
Average Output Current	I_O	Rectangular wave	2.0	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	20	A
Junction Temperature	Tj		−55 to +125	°C
Storage Temperature	Tstg		−55 to +125	°C

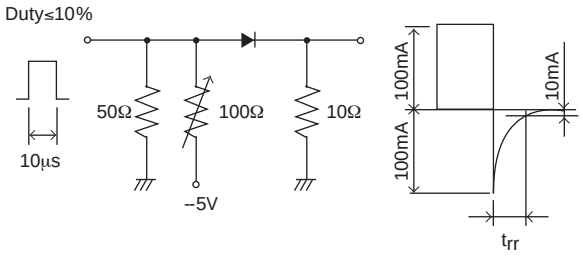
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[MOSFET]						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−1mA, V_{GS}=0V	−20			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=−20V, V_{GS}=0V			−1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=−10V, I_D=−1mA	−0.4		−1.3	V
Forward Transfer Admittance	| yfs |	V_{DS}=−10V, I_D=−1.5A		3.6		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=−1.5A, V_{GS}=−4.5V		65	85	mΩ
	R_{DS}(on)2	I_D=−1A, V_{GS}=−2.5V		98	137	mΩ
	R_{DS}(on)3	I_D=−0.5A, V_{GS}=−1.8V		155	235	mΩ
Input Capacitance	Ciss	V_{DS}=−10V, f=1MHz		320		pF
Output Capacitance	Coss			66		pF
Reverse Transfer Capacitance	Crss			50		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		7.1		ns
Rise Time	t_r			21		ns
Turn-OFF Delay Time	t_d(off)			37		ns
Fall Time	t_f			32		ns
Total Gate Charge	Qg	V_{DS}=−10V, V_{GS}=−4.5V, I_D=−3A		4.0		nC
Gate-to-Source Charge	Qgs			0.6		nC
Gate-to-Drain “Miller” Charge	Qgd			1.1		nC
Diode Forward Voltage	V_{SD}	I_S=−3A, V_{GS}=0V		−0.83	−1.2	V
[SBD]						
Reverse Voltage	V_R	I_R=1mA	15			V
Forward Voltage	V_F1	I_F=1.0A		0.33	0.39	V
	V_F2	I_F=2.0A		0.39	0.46	V
Reverse Current	I_R	V_R=7.5V			300	μA
Interterminal Capacitance	C	V_R=10V, f=1MHz		35		pF

Switching Time Test Circuit
(MOSFET)

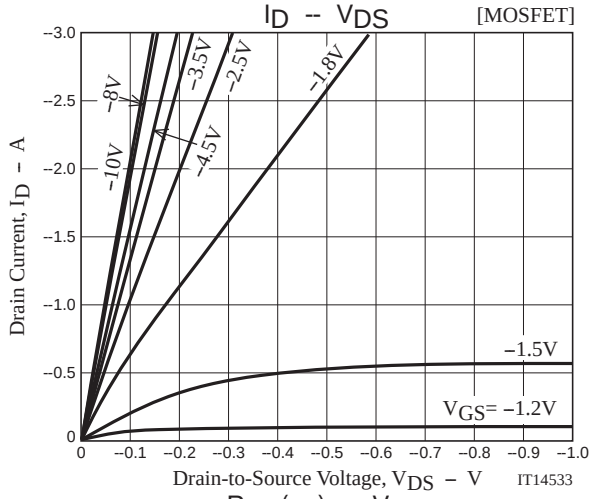


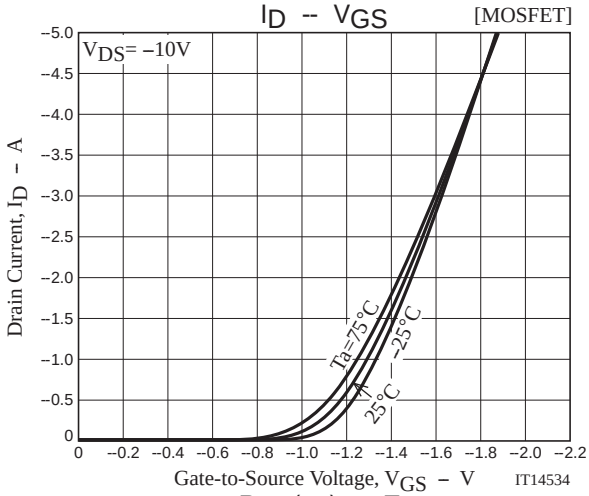
t_{rr} Test Circuit
(SBD)

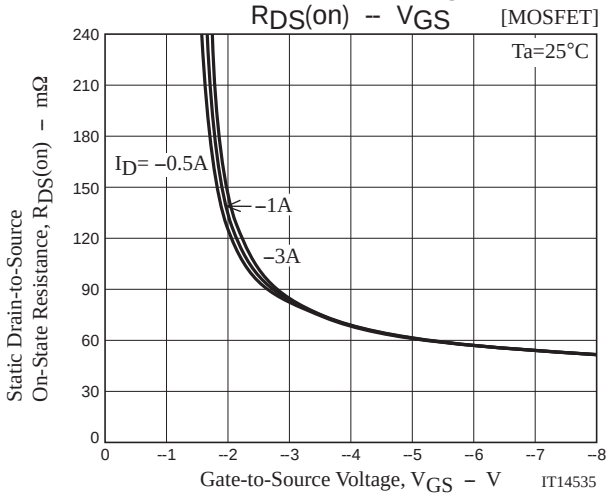


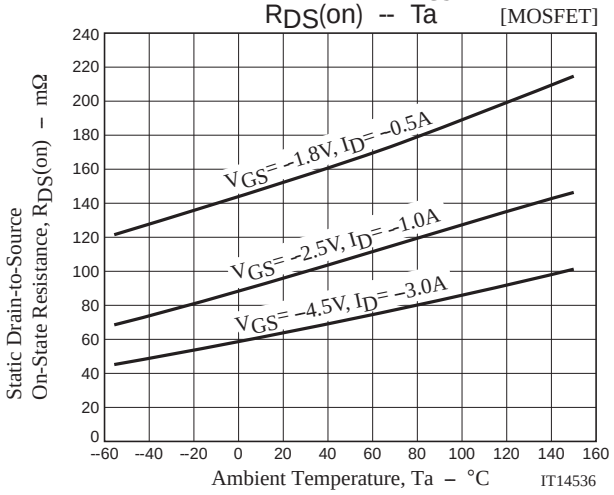
Ordering Information

Device	Package	Shipping	memo
EMH2801-TL-H	EMH8	3,000pcs./reel	Pb Free and Halogen Free

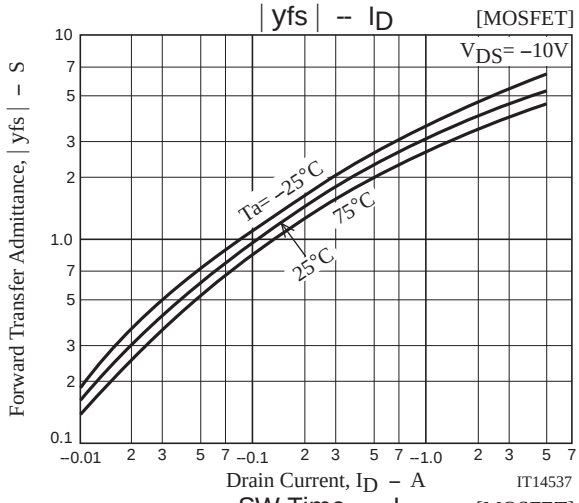




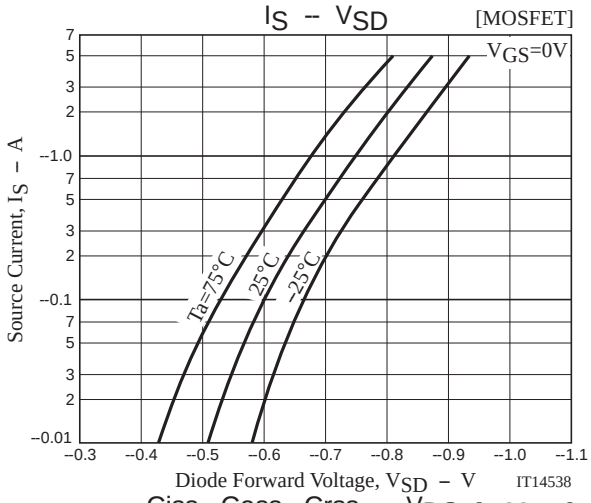




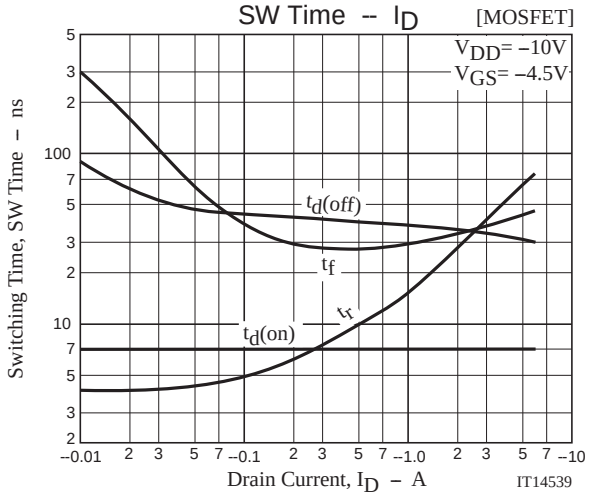
IT14535



IT14537



IT14538



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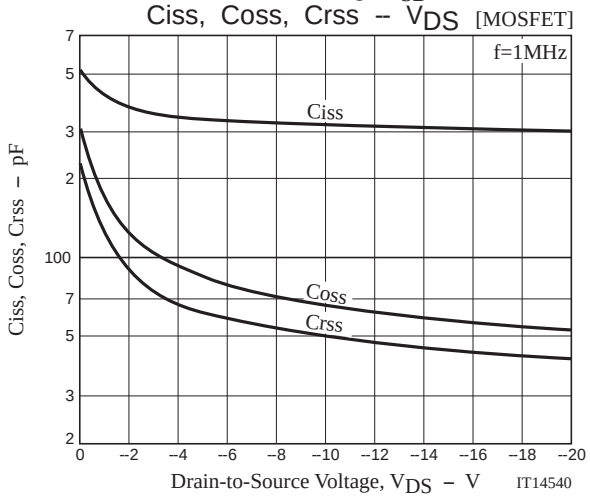
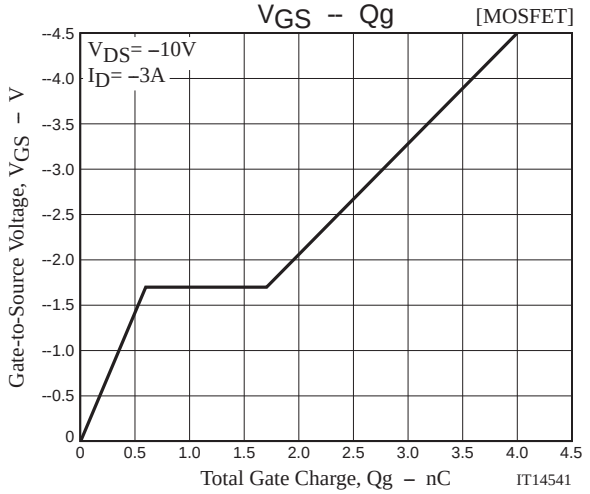


IT14540



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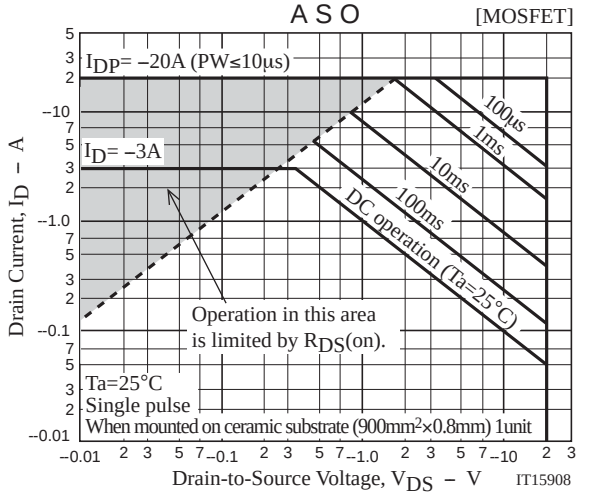
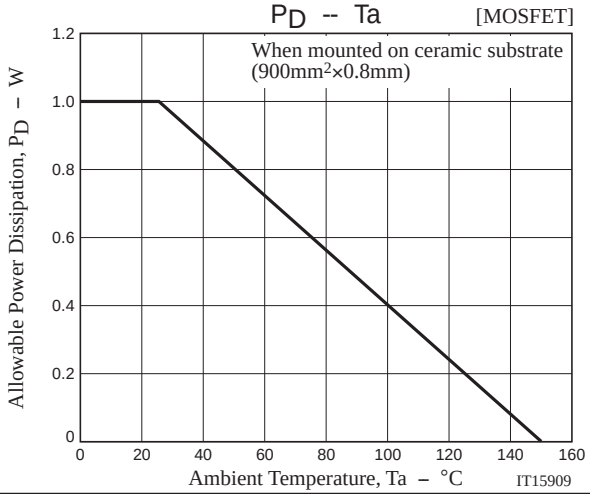
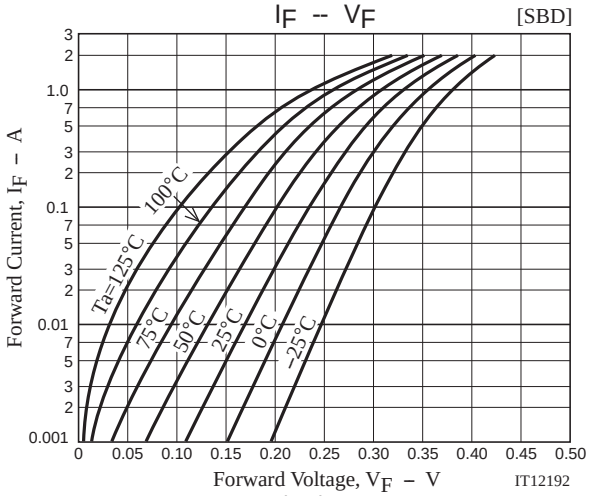


IT15908

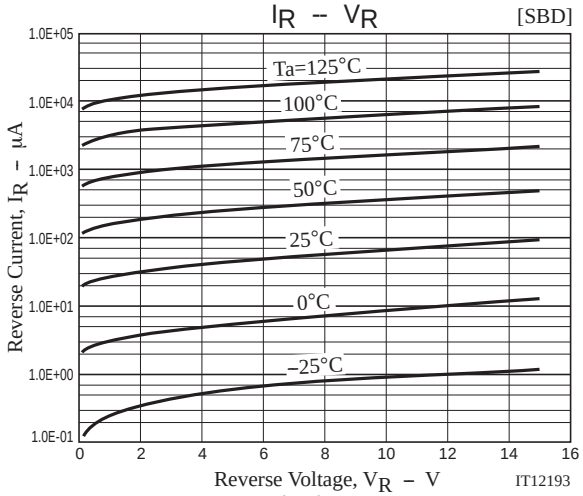


IT15909

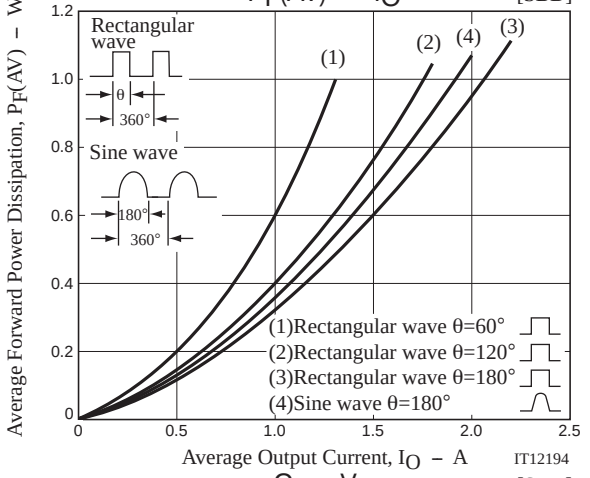
I_F -- V_F [SBD]



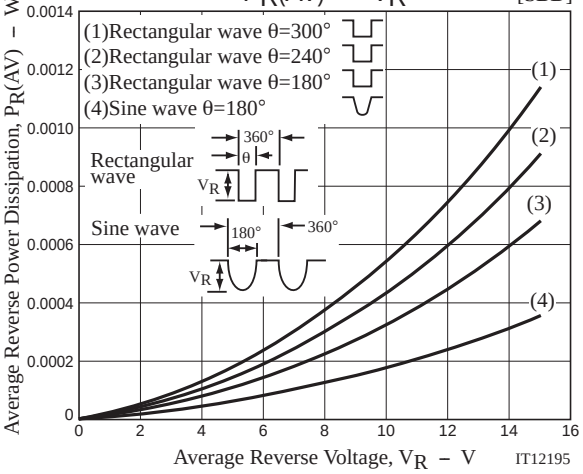
I_R -- V_R [SBD]



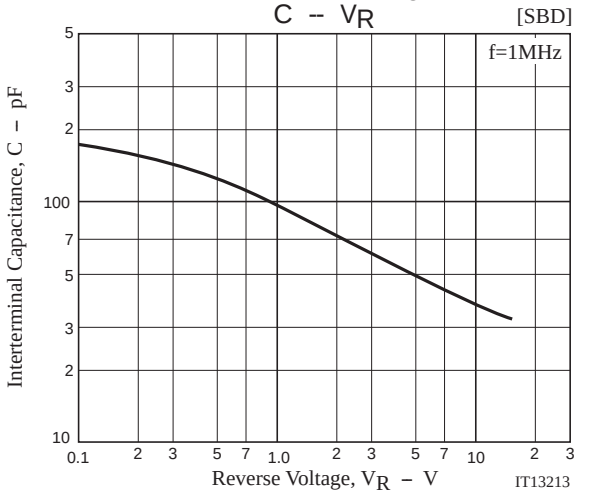
$P_{F(AV)}$ -- I_O [SBD]



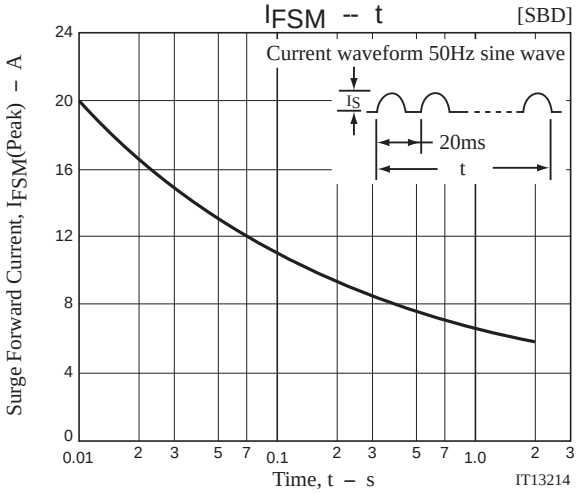
$P_{R(AV)}$ -- V_R [SBD]



C -- V_R [SBD]



I_{FSM} -- t [SBD]



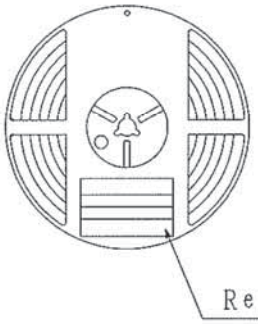
Embossed Taping Specification

EMH2801-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
EMH8	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

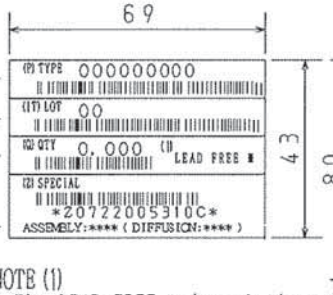
Packing method



Reel label

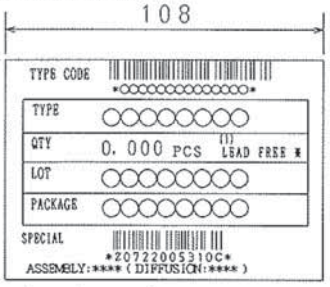
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



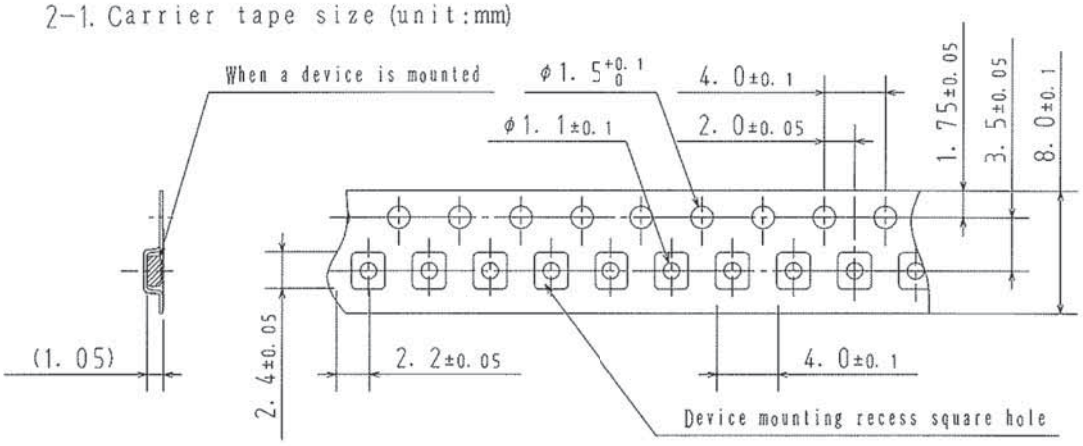
NOTE (1)

The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

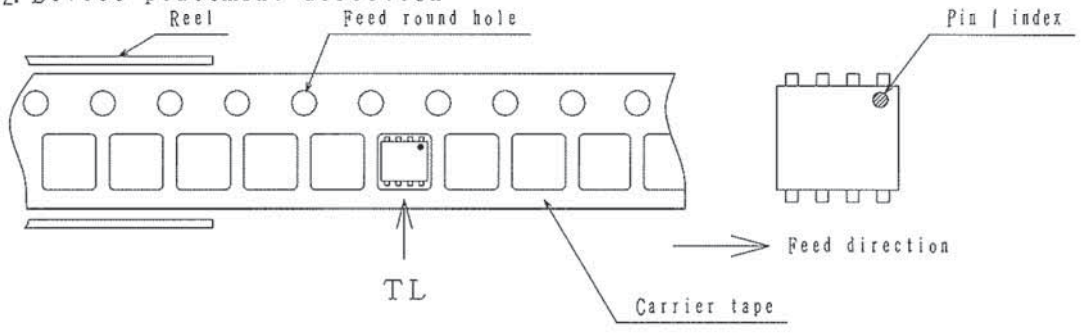
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



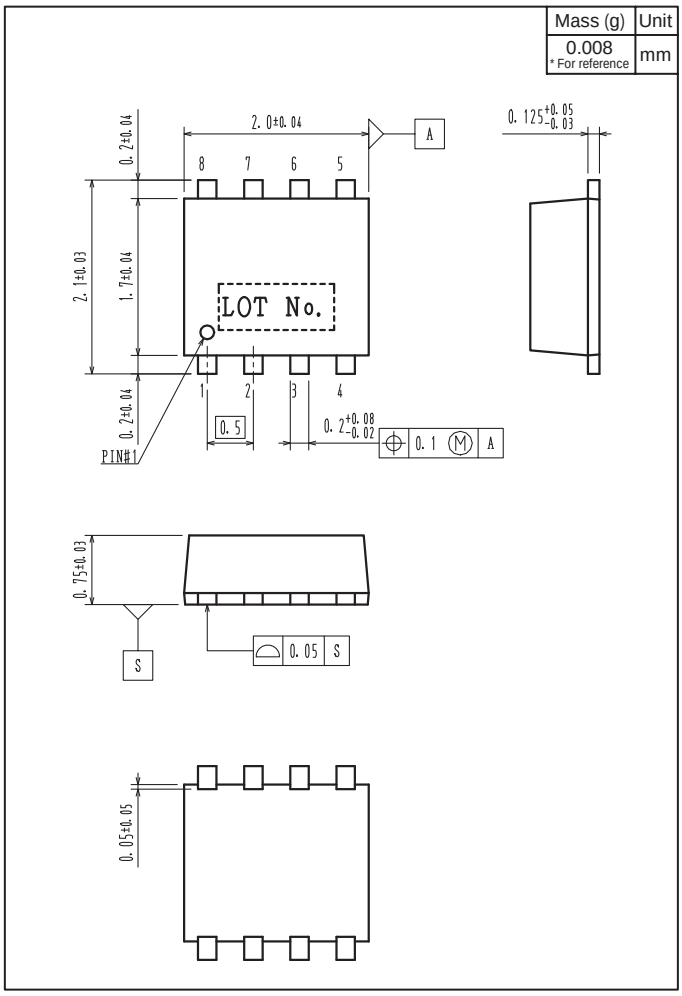
2-2. Device placement direction



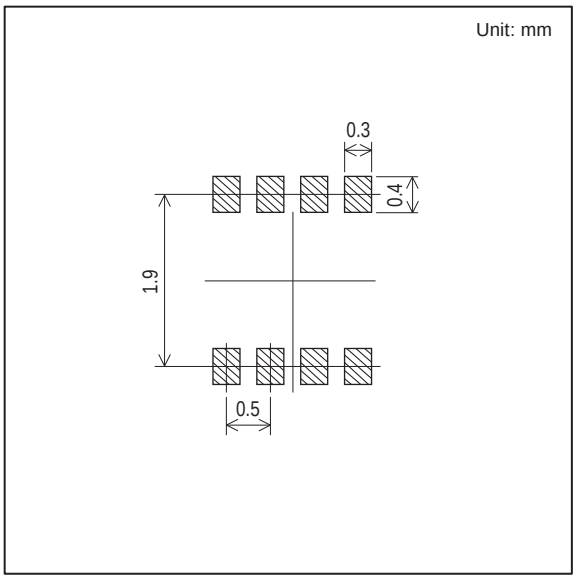
Those with pin 1 index on the feed hole side·····TL

Outline Drawing

EMH2801-TL-H



Land Pattern Example



Note on usage : Since the EMH2801 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

This catalog provides information as of June, 2012. Specifications and information herein are subject to change without notice.